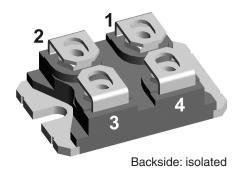


 $V_{RRM} = 1200 V$ $I_{FAV} = 2x 41 A$

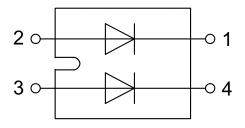
SiC Schottky Diode

Ultra fast switching Zero reverse recovery

Part number **DCG85X1200NA**



UL pending



Features / Advantages:

- · Ultra fast switching
- Zero reverse recovery
- Zero forward recovery
- Temperature independent switching behavior
- · Positive temperature coefficient of forward voltage
- Tvjm = 175°C

Applications:

- Solar inverter
- Uninterruptible power supply (UPS)
- Welding equipment
- Switched-mode power supplies
- Medical equipment
- High speed rectifier

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate with Aluminium nitride isolation for low thermal resistance
- Advanced power cycling

Terms & Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. dered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you. Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
 to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, test conditions and dimensions.

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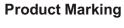
SiC Diode (per leg)				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	
V _{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V _{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I _R	reverse current	$V_R = V_{RRM}$ $T_{VJ} = 25^{\circ}C$ $T_{VJ} = 175^{\circ}C$		70 130	400 800	μA μA
V _F	forward voltage	$I_F = 20 \text{ A}$ $T_{VJ} = 25^{\circ}\text{C}$ $I_F = 40 \text{ A}$		1.5	1.8	V
		$I_F = 20 \text{ A}$ $T_{VJ} = 175^{\circ}\text{C}$ $I_F = 40 \text{ A}$		2.20	3.0	V
I _{FAV}	average forward current	$T_{C} = 80^{\circ}C$ rectangular, $d = 0.5$ $T_{C} = 100^{\circ}C$ $T_{VJ} = 175^{\circ}C$			41 36	A A
I _{F25} I _{F80} I _{F100}	forward current	based on typ. V_{F0} and r_{F} $ T_{C} = 25^{\circ}C $ $ T_{C} = 80^{\circ}C $ $ T_{C} = 100^{\circ}C $			73 56 49	A A A
I _{FSM}	max forward surge current	t = 10 ms,half sine (50 Hz) $t_P = 10 \mu s$, pulse $T_{VJ} = 25^{\circ}C$ $V_R = 0V$			1150	A A
V _{F0}	threshold voltage	$T_{VJ} = 125^{\circ}C$		0.80		V
r _F	slope resistance	$\label{eq:total_for_power_loss} \begin{cases} & 175^{\circ}\text{C} \\ & \text{T}_{\text{VJ}} = & 125^{\circ}\text{C} \\ & 175^{\circ}\text{C} \end{cases}$		0.73 28.4 35.2		V m Ω
Q _c	total capacitive charge	$V_R = 800 \text{ V}, I_F = 40 \text{A}$ $T_{VJ} = 25^{\circ}\text{C}$ $dI/dt = 400 \text{ A}/\mu\text{s}$		200		nC
С	total capacitance	$ \begin{array}{c} V_{\text{R}} = 0 \; V \\ V_{\text{R}} = 400 \; V \\ V_{\text{R}} = 800 \; V \end{array} \right\} \hspace{0.5cm} T_{\text{VJ}} = 25^{\circ}\text{C, f} = 1 \; \text{MHz} $		3000 185 135		pF pF pF
R_{thJC} R_{thJH}	thermal resistance junction to case thermal resistance junction to heatsink	with heatsink compound; IXYS test setup		0.72	0.60	K/W K/W

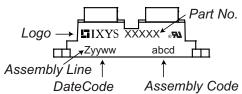




Package	e Outlines SOT-227B (minibloc)		Ratings				
Symbol	Definitions	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				100	Α
T _{stg}	storage temperature			-40		150	°C
T _{op}	operation temperature			-40		150	°C
T _{VJ}	virtual junction temperature			-40		175	°C
Weight					30		g
M _D	mounting torque 1)	screws to heats	sink			1.5	Nm
		terminal connec	terminal connection screws			1.3	Nm
d_{Spp}	Spp		terminal to terminal	10.5			mm
d_{Spb}	creepage distance on surface		terminal to backside				mm
d _{App}			terminal to terminal	3.2			mm
d _{Apb}	striking distance through air		terminal to backside	6.8			mm
V _{ISOL}	isolation voltage	t = 1 second	ond $50 / 60$ Hz, RMS; $I_{ISOI} \le 1$ mA				V
		t = 1 minute	JO / JO TIZ, TIMJ, I _{ISOL} ≤ TIMA	2500			V
C _P	coupling capacity per switch	between shorted to lization	erminals of diodes and back side metal-				pF

¹⁾ further information see application note IXAN0073 on www.ixys.com/TechnicalSupport/appnotes.aspx (General / Isolation, Mounting, Soldering, Cooling)





Part description

D = Diode

C = SiC

G = SIC G = extreme fast 85 = Current Rating [A] X = Parallel legs 1200 = Reverse Voltage [V] NA = SOT-227 (minibloc)

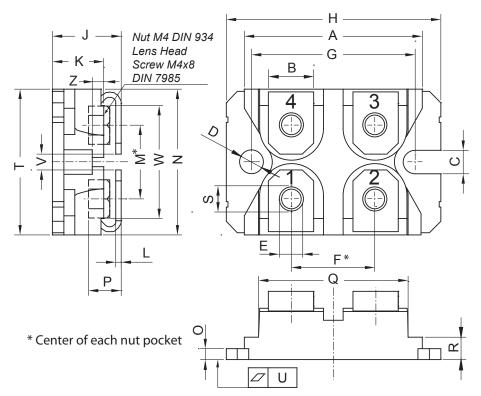
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	DCG85X1200NA	DCG85X1200NA	Tube	10	520214

Equivalent Circuits for Simulation *on die level, typical				
$I \rightarrow V_0$		T _{vJ} = 125°C	T _{VJ} = 175°C	
$V_{0 \text{ max}}$	threshold voltage	0.80	0.73	V
$R_{0 max}$	slope resistance *	28.4	35.2	mΩ

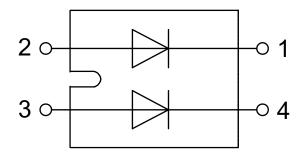




Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches			
Diiii.	min	max	min	max		
Α	31.50	31.88	1.240	1.255		
В	7.80	8.20	0.307	0.323		
С	4.09	4.29	0.161	0.169		
D	4.09	4.29	0.161	0.169		
Е	4.09	4.29	0.161	0.169		
F	14.91	15.11	0.587	0.595		
G	30.12	30.30	1.186	1.193		
Н	37.80	38.23	1.488	1.505		
٦	11.68	12.22	0.460	0.481		
K	8.92	9.60	0.351	0.378		
L	0.74	0.84	0.029	0.033		
М	12.50	13.10	0.492	0.516		
Ν	25.15	25.42	0.990	1.001		
0	1.95	2.13	0.077	0.084		
Р	4.95	6.20	0.195	0.244		
Ю	26.54	26.90	1.045	1.059		
R	3.94	4.42	0.155	0.167		
S	4.55	4.85	0.179	0.191		
Т	24.59	25.25	0.968	0.994		
U	-0.05	0.10	-0.002	0.004		
V	3.20	5.50	0.126	0.217		
W	19.81	21.08	0.780	0.830		
Z	2.50	2.70	0.098	0.106		





SiC Diode (per leg)

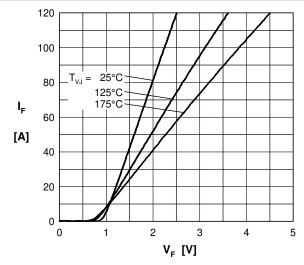


Fig. 1 Typ. forward characteristics

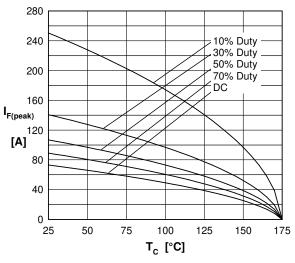


Fig. 3 Typ. current derating

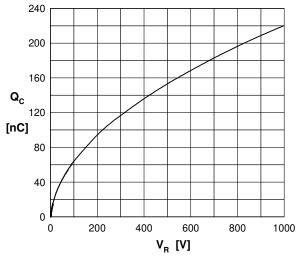


Fig. 5 Typ. recovery charge vs. reverse voltage

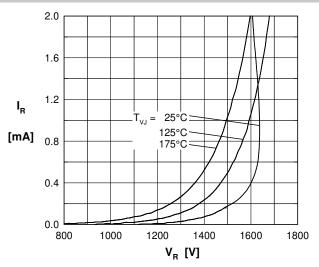


Fig. 2 Typ. reverse characteristics

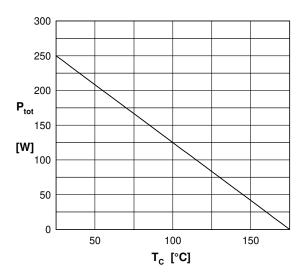


Fig. 4 Power derating

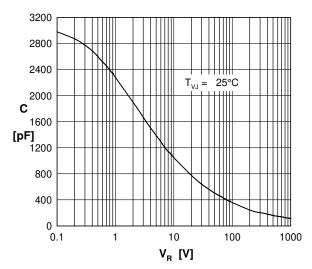


Fig. 6 Typ. junction capacitance vs. reverse Voltage

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SiC Diode (per leg)

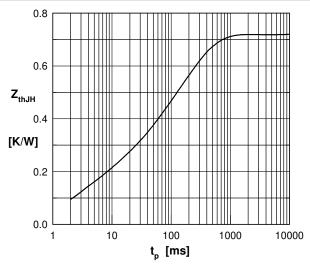


Fig. 7 Typ. transient thermal impedance

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